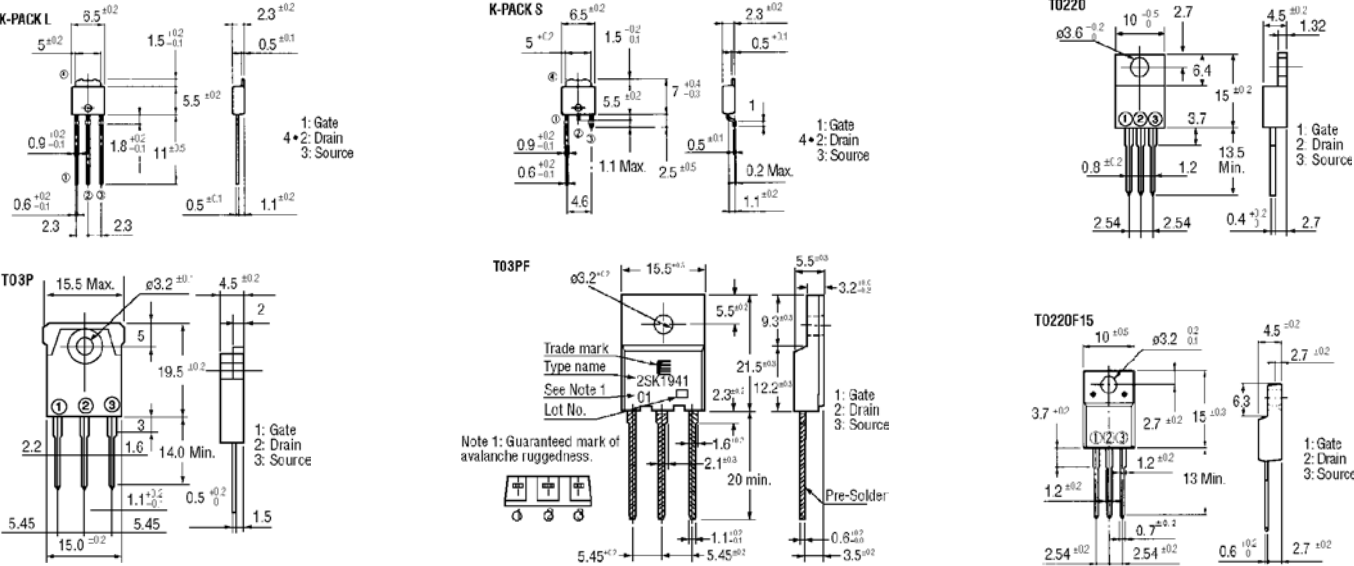


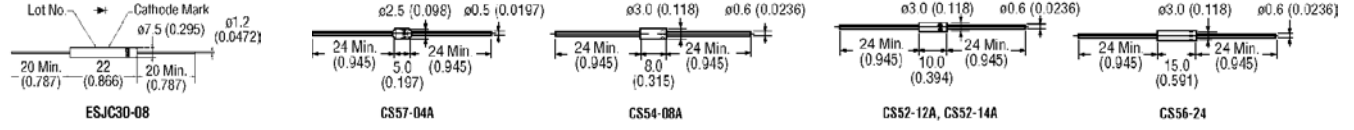
N-Channel Silicon Power MOS-FET



- F-I Series = Low RDS(ON)
- F-II Series = VGS ±30 V, Reduced Turn Off Time
- FAP-II Series = High Avalanche Ruggedness
- F-III Series = Logic Level, High g_m
- FAP-III = Logic Level, High Avalanche Ruggedness
- FAP-IIS = VGS ±35 V, VGS(th) 4.0 ±0.5 V
- FAP-IIA = Reduced Turn Off Time
- FAP-IIIBH = High Speed Non Logic
- FAP-IIIB = Logic Level, VGS(th) 1.5 ±0.5 V

Mfr.'s Type	Series	Ratings			Characteristics						Package
		V _{GS} (V)	I _D (A)	P _D (W)	R _{DS(ON)} (Ω) (Max.)		C _{iss} (pF)	C _{oss} (pF)	t _{on} (ns)	t _{off} (ns)	
					V _{GS} =4V	V _{GS} =10V					
2SJ314-01L	FAP-III	-60	-5.0	20	0.480	0.300	750	300	53	270	K-PACK L
2SJ314-01S	FAP-III	-60	-5.0	20	0.480	0.300	750	300	53	270	K-PACK S
2SK2248-01L	FAP-III	30	35.0	60	0.037	0.022	2630	1200	188	720	K-PACK L
2SK2248-01S	FAP-III	30	35.0	60	0.037	0.022	2630	1200	188	720	K-PACK S
2SK2687-01	FAP-III	30	50.0	60	0.017	0.010	4130	1950	103	520	T0220
2SK2893-01	FAP-IIIB	30	100.0	150	0.007	0.004	9900	4950	260	1270	T03P
2SK2900-01	FAP-IIIBH	60	45.0	60	—	0.140	3450	1370	110	200	T0220
2SK2690-01	FAP-III	60	80.0	125	0.017	0.010	5250	1870	143	450	T03P
2SK2906-01	FAP-IIIBH	60	100.0	150	—	0.007	8100	3150	400	470	T03P
2SK3270-01	Trench	60	80.0	135	—	0.006	9000	1250	250	285	T0-220
2SK3271-01	Trench	60	100.0	155	—	0.006	9000	1250	250	285	T03P
2SK3216-01	FAP-IIIBH	100	45.0	80	—	0.026	4800	1140	186	240	T0220
2SK3217-01MR	FAP-IIIBH	100	50.0	70	—	0.025	4800	1140	230	265	T0-220F15
2SK3218-01	FAP-IIIBH	150	35.0	80	—	0.048	3900	800	158	270	T0220
2SK3219-01MR	FAP-IIIBH	150	40.0	70	—	0.043	3980	830	174	263	T0-220F15
2SK2521-01	FAP-II	200	18.0	50	—	0.180	1650	330	150	150	T0220
2SK3262-01MR	FAP-IIIB	200	20.0	45	0.15	0.100	2550	435	85	520	T0-220F15
2SK900	F-I	250	12.0	80	—	0.300	1800	300	75	260	T0220
2SK902	F-I	250	30.0	150	—	0.100	3900	900	200	1000	T03P
2SK1017-01	F-II	450	20.0	150	—	0.350	3300	480	375	740	T03P
2SK2021-01	FAP-IIA	500	5.0	60	—	1.600	1500	130	55	100	T0220
2SK2642-01MR	FAP-IIS	500	15.0	50	—	0.550	2100	380	220	230	T0220F15
2SK2757-01	FAP-IIS	500	10.0	80	—	0.900	950	180	25	60	T0220
2SK725	F-I	500	15.0	125	—	0.380	4000	500	130	440	T03P
2SK1941-01R	FAP-IIA	600	16.0	100	—	0.550	4950	470	165	420	T03PF
2SK2646-01	FAP-II	800	4.0	80	—	4.000	450	75	20	50	T0220
2SK956-01	FAP-II	800	9.0	150	—	1.500	2100	300	425	690	T03P
2SK2648-01	FAP-IIS	800	9.0	150	—	1.500	1200	180	30	95	T03P
2SK2654-01	FAP-IIS	900	8.0	150	—	2.000	1200	180	30	95	T03P
2SK2082-01	FAP-IIA	900	9.0	150	—	1.400	3300	320	130	320	T03P
2SK1986-01	FAP-II	1000	4.0	80	—	3.600	1950	150	55	160	T0220
2SK2258-01	FAP-II	1000	4.0	100	—	3.600	1950	150	55	160	T03P

Fast Recovery High Voltage Silicon Rectifiers



Mfr.'s Type†	Repetitive Peak Reverse Voltage V _{RRM}	Average Forward Current I _F *	Non-Repetitive Peak Surge Current I _{FSM} **	Maximum Forward Voltage Drop (at 1 mA, T _s = 25°C) V _{FM}	Maximum Reverse Current Repetitive (at V _{RRM} , T _s = 25°C) I _{RRM}	Maximum Junction Capacitance (at V _{RRM} = 0V, T _s = 25°C) @ 1 MHz
	kV	mA	A	Volts	μA	pF
ESJC30-08	12	300	15.0	16.0	10	—
CS57-04A	4	25	1.0	15.0	1	2
CS54-08A	8	25	1.0	30.0	1	2
CS52-12A	12	10	0.5	45.0	1	1
CS52-14A	14	10	0.5	51.0	1	1
CS56-24	24	10	0.5	75.0	1	1

Notes: *Single phase; half sine wave in oil bath or filled epoxy at ambient temperature 25°C. **1/2 cycle, 60 Hz at full load. †Reverse Recovery Time: "A" Type — 80 nsec max. @ T_s = 25°C, I_F = 2 mA, I_R = 1 mA; Non "A" Type — 100 nsec max. @ T_s = 25°C, I_F = 2 mA, I_R = 1 mA. Storage and Operating Junction Temperature, T_J -65°C to +150°C. Packaging: Bulk or tape and reel available (please specify).

Same Day Shipments For Product In Stock

ALLIED ► 803